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#### Abstract of the Disclosure

[0043] A method for forming a patterned silicon-containing layer is disclosed. The method includes providing a substrate, providing a polysilicon layer on the substrate, providing a hard mask layer on the polysilicon layer, patterning and etching the hard mask layer and etching the polysilicon layer according to the pattern of the hard mask layer using a fluorine-containing etchant gas. The resulting sidewall profile of the etched polysilicon layer is substantially straight, uniform and devoid of a necking or notched configuration.